

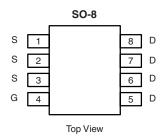
# **N-Channel 30-V MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
30	0.007 at V <sub>GS</sub> = 10 V	16		
30	0.0085 at V <sub>GS</sub> = 4.5 V	14		

#### **FEATURES**

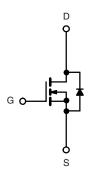
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs
- 100 % R<sub>g</sub> Tested





Ordering Information: Si4874BDY-T1-E3 (Lead (Pb)-free)

Si4874BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Dunis Comment /T 450 °C)	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	16	12	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		13	9	
Pulsed Drain Current		I <sub>DM</sub>	± 50		А
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.7	1.40	l
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.0	1.6	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	T D	2.0	1.0	] <b>v</b> v
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipular languism to Austriant (MOOFFT)	t ≤ 10 s	R <sub>thJA</sub>	34	41	
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	Steady State	' <sup>1</sup> thJA	68	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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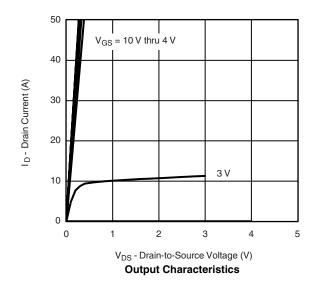
MOSFET SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$ 1.0			3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	lass	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1 ,,,		
Zero Gate Voltage Diam Guirent	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	) V 30			Α	
	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16 A		0.0057	0.007	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 14 \text{ A}$		0.0068	0.0085		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 16 A		65		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.74	1.1	V	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			3230			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		585		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			255		1	
Total Gate Charge	$Q_g$			21	25		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 16 \text{ A}$		9.5		nC	
Gate-Drain Charge	$Q_{gd}$			6.5		1	
Gate Resistance	$R_{g}$		0.4	0.9	1.4	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			16	25		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		10	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		57	90	ns	
Fall Time	t <sub>f</sub>			15	25		
Source-Drain Reverse Recovery Time t <sub>ri</sub>		I <sub>F</sub> = 2.7 A, dI/dt = 100 A/μs		40	60		

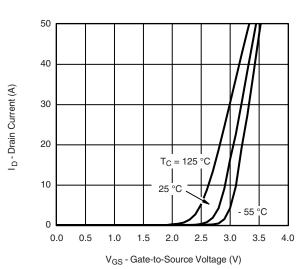
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

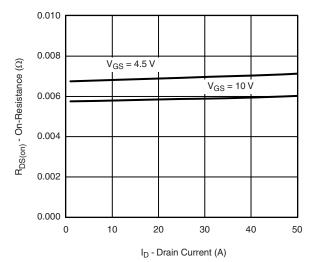




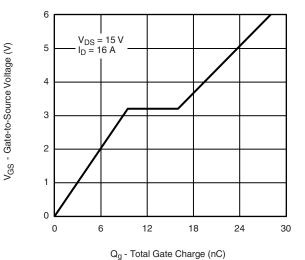
**Transfer Characteristics** 



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



#### On-Resistance vs. Drain Current



T<sub>J</sub> = 150 °C

T<sub>J</sub> = 150 °C

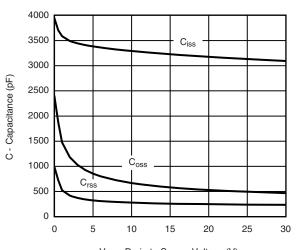
T<sub>J</sub> = 25 °C

10

1
0.00
0.2
0.4
0.6
0.8
1.0
1.2

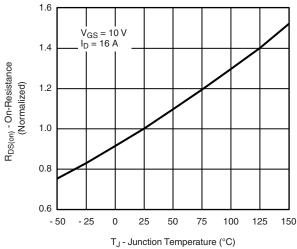
**Gate Charge** 

V<sub>SD</sub> - Source-to-Drain Voltage (V) **Source-Drain Diode Forward Voltage** 

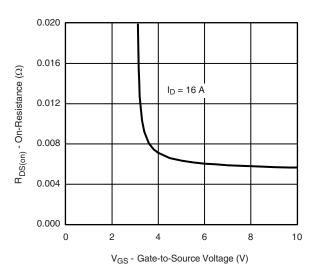


V<sub>DS</sub> - Drain-to-Source Voltage (V)





## On-Resistance vs. Junction Temperature



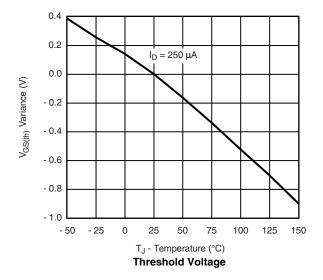
On-Resistance vs. Gate-to-Source Voltage

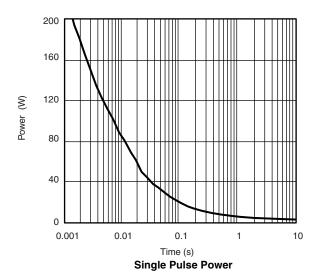
Is - Source Current (A)

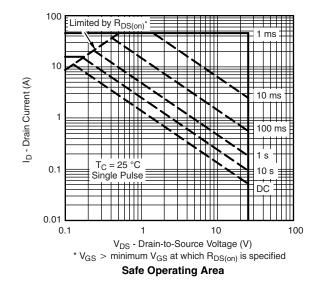
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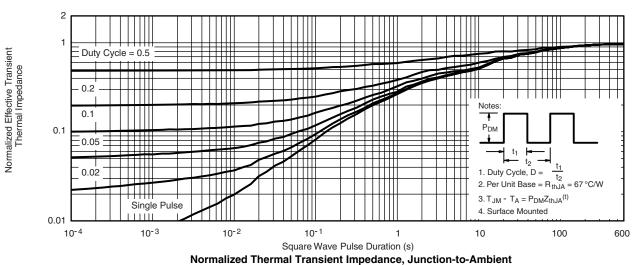
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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



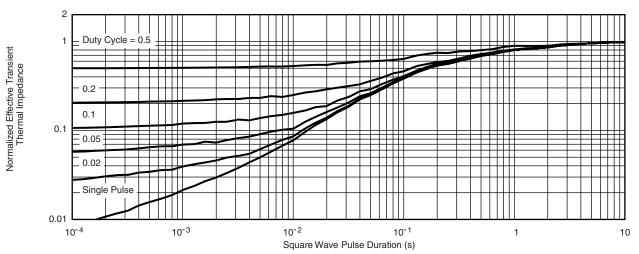








## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

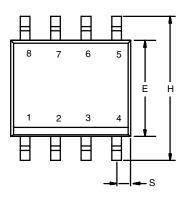


Normalized Thermal Transient Impedance, Junction-to-Foot

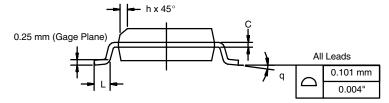
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**SOIC (NARROW): 8-LEAD** JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050	0.050 BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

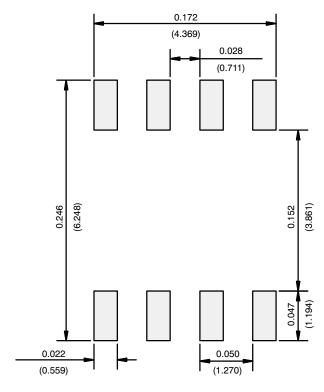
DWG: 5498

Document Number: 71192 www.vishay.com 11-Sep-06

# Vishay Siliconix



#### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOT

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